

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (CURRENTLY AMENDED) A high-frequency semiconductor device, comprising:
 - an amplifier;
 - a dielectric substrate provided on an input side or an output side of the amplifier;
 - a plurality of transmission lines formed on a surface of the dielectric substrate and connected electrically to the amplifier, the transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency; and
 - ~~a thin film resistor formed on the surface of the dielectric substrate and connected electrically between the plurality of to the transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant.~~
- 2-22. (CANCELED)
23. (NEW) A high-frequency semiconductor device, comprising:
 - first and second amplifiers;
 - a dielectric substrate provided on an input side or an output side of the first and second amplifiers;
 - a first transmission line formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first transmission line having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;
 - a second transmission line formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the second transmission line having an electrical length substantially $\lambda/4$ with respect to an operation frequency; and
 - a thin film resistor connected electrically between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant.

24. (NEW) A high-frequency semiconductor device; comprising:
first and second amplifier;
a dielectric substrate provided on an input side or an output side of the first and second amplifiers;
a first transmission line formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first transmission line having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;
a second transmission line formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the second transmission line having an electrical length substantially $\lambda/4$ with respect to an operation frequency;
a third transmission line formed on a surface of the dielectric substrate between the first and second transmission lines, the third transmission line having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;
a first thin film resistor connected electrically between the first and third transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant; and
a second thin film resistor connected electrically between the second and third transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant.
25. (NEW) A high-frequency semiconductor device, comprising:
first and second amplifiers;
a dielectric substrate provided on an input side or an output side of the first and second amplifiers;
first and second transmission lines formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first and second transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;
third and fourth transmission lines formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the third and fourth transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;
a first thin film resistor connected between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a second thin film resistor connected between the second and third transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant; and

a third thin film resistor connected between the third and fourth transmission lines and disposed in a passing direction of an electrical power so as to distributed constant.

26. (NEW) A high-frequency semiconductor device, comprising:

first and second amplifiers;

a dielectric substrate provided on an input side or an output side of the first and second amplifiers;

first and second transmission lines formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first and second transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

third and fourth transmission lines formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the third and fourth transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a fifth transmission line formed between the second and third transmission lines, the fifth transmission line having a electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a first thin film resistor connected between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a second thin film resistor connected between the third and fourth transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant; and

a third thin film resistor connected between the second and third transmission lines and disposed in a passing direction of an electrical power so as to distributed constant; and

a fourth thin film resistor connected between the fifth and third transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant.

27. (NEW) A high-frequency semiconductor device, comprising:

first and second amplifiers;

a dielectric substrate provided on an input side or an output side of the first and second amplifiers;

first and second transmission lines formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first and second transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

third and fourth transmission lines formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the third and fourth transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a first thin film resistor connected between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a second thin film resistor connected between the third and fourth transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant; and

a third thin film resistor connected to an end of the second transmission line opposed to the third transmission line;

a fourth thin film resistor connected to an end of the third transmission line opposed to the second transmission line; and

a unit for connecting the third and fourth thin film resistors electrically.

28. (NEW) A high-frequency semiconductor device, comprising:

first and second amplifiers;

a dielectric substrate provided on an output side or an input side of the first and second amplifiers;

first and second transmission lines formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first and second transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

third and fourth transmission lines formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the third and fourth transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a first thin film resistor connected between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a second thin film resistor connected between the third and fourth transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a first input terminal or output terminal on a power combining circuit connected electrically to a side of the first and second transmission lines opposite to a side thereof connected to the first amplifier;

a second input terminal or output terminal on the power combining circuit connected electrically to a side of the third and fourth transmission lines opposite to a side thereof connected to the second amplifier; and

a third thin film resistor connected between the first input terminal and the second input terminal or between the first output terminal and the second output terminal.

29. (NEW) A high-frequency semiconductor device, comprising:

first and second amplifiers;

a dielectric substrate provided on an output side or an input side of the first and second amplifiers;

first and second transmission lines formed on a surface of the dielectric substrate and connected electrically to the first amplifier, the first and second transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

third and fourth transmission lines formed on a surface of the dielectric substrate and connected electrically to the second amplifier, the third and fourth transmission lines having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a first thin film resistor connected between the first and second transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a second thin film resistor connected between the third and fourth transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a fifth transmission line formed between the second and third transmission lines, the fifth transmission line having an electrical length of substantially $\lambda/4$ with respect to an operation frequency;

a third thin film resistor connected between the second and fifth transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a fourth thin film resistor connected between the fifth and third transmission lines and disposed in a passing direction of an electrical power so as to form a distributed constant;

a first input terminal or output terminal on a power combining circuit connected electrically to a side of the first and second transmission lines opposite to a side thereof connected to the first amplifier; and

a second input terminal or output terminal on the power combining circuit connected electrically to a side of the third and fourth transmission lines opposite to a side thereof connected to the second amplifier.